SEM	ICONDUCTOR M				
FDC	6324L				
Integ	grated Load Switch				
General	Description		Features		
These Ir proprieta density resistanc devices switch ap are neede	ntegrated Load Switches are produ ry, high cell density, DMOS techno process is especially tailored to e and provide superior switching are particularly suited for low vol oplication where low conduction loss ed.	and the second s	 V_{DROP}=0.2V @ V_{DROP}=0.3V @ High density ce V_{ON/OFF} Zener Body Model. SuperSOTTM-6 thermal and ele 	V_{IN} =12V, I _L =1A, V _{ON/OFF} = V _{IN} =5V, I _L =1A, V _{ON/OFF} = ell design for extremely lo protection for ESD rugged package design using co actrical capabilities.	=1.5 to 8V 1.5 to 8V. w on-resistance. dness. >6KV Huma pper lead frame for sup
	÷ W	-			
SOT-	23 SuperSOT™ 6	SuperSOT™ 9			SOIC-16
	pin 1	0N/0FF 5 R1,C1 6		Vout,C1	• • • • • • • • • • • • • • • • • • •
Supe	pin 1 erSOT ™6	ON/OFF 5 R1,C1 6 See Ag	Q2 Q1 1 pplication Circuit	Vout,C1 ON/OFF R2	• • • • • • • • • • • • • • • • • • •
Supe Absolu	erSOT TM -6 te Operating Range $T_A = Parameter$	ON/OFF 5 R1,C1 6 See Ag	Q2 2 pplication Circuit	Vout,C1 N ON/OFF R2 FDC6324L	v ou
Supe Absolu Symbol	erSOT TM 6 te Operating Range $T_A = \frac{Parameter}{Input Voltage Range}$	ON/OFF 5 R1,C1 6 See Aj	Q2 2 2 pplication Circuit	Vout,C1 N ON/OFF R2 FDC6324L 3 - 20	v ou
Supe Absolu Symbol V _{IN} V _{ONOFF}	erSOT [™] 6 Parameter Input Voltage Range ON/OFF Voltage Range	ON/OFF 5 R1,C1 6 See Ag	Q2 2 2 2 2 1 1 2 0 1	Vout,C1 R2 FDC6324L 3 - 20 1.5 - 8	V
Supe Absolu Symbol VIN VONVOFF	erSOT [™] 6 te Operating Range T _A = Parameter Input Voltage Range ON/OFF Voltage Range Load Current @ V _{DROP} =0.5V - Cor	N/OFF 5 R1,C1 6 See Aj 25°C unless otherwise noted	Q2 2 2 pplication Circuit	Vout,C1 N ON/OFF R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5	Unit
Supe Absolu Symbol V _{IN} V _{ONOFF} IL	erSOT [™] 6 Parameter Input Voltage Range ON/OFF Voltage Range Load Current @ V _{DROP} =0.5V - Cor Maximum Power Dissipation	e 25°C unless otherwise noted	Q2 2 2 pplication Circuit	Vout,C1 R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5 0.7	V OU
Supe Absolu Symbol V _{IN} V _{ON/OFF} I _L P _D T _J , T _{STG}	erSOT [™] 6 te Operating Range T _A = Parameter Input Voltage Range ON/OFF Voltage Range Load Current @ V _{DROP} =0.5V - Cor Maximum Power Dissipation Operating and Storage Temperatur	e 25°C unless otherwise noted	a2 2 2 pplication Circuit	Vout,C1 N ON/OFF R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5 0.7 -55 to 150	V OU
Supe Absolu Symbol V _{IN} V _{ONOFF} I L P _D T _J , T _{STG} ESD	erSOT [™] 6 Parameter Input Voltage Range ON/OFF Voltage Range ON/OFF Voltage Range Load Current @ V _{DROP} =0.5V - Cor Maximum Power Dissipation Operating and Storage Temperatur Electrostatic Discharge Rating MIL Model (100pf/15000hm)	e 25°C unless otherwise noted e 25°C unless otherwise noted ntinuous (Note 1) - Pulsed (Note 1 & 3) (Note 2a) re Range -STD-883D Human Body	Q2 2 2 2 1 1 1 1 1 1 1 1 1 1 1 1 1	Vout,C1 N ON/OFF R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5 0.7 -55 to 150 6	V V V V V V V V V V
Supe Absolu Symbol V _{IN} V _{ON/OFF} I L P _D T _J , T _{STG} ESD THERMA	erSOT [™] 6 T _A = Parameter Input Voltage Range ON/OFF Voltage Range Load Current @ V _{DROP} =0.5V - Cor Maximum Power Dissipation Operating and Storage Temperatur Electrostatic Discharge Rating MIL Model (100pf/1500Ohm) L CHARACTERISTICS	Convorf 5 Convorf 5 Convort 1 Convort 1 Convort 2 Convo	a2 2 2 pplication Circuit	Vout,C1 N ON/OFF R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5 0.7 -55 to 150 6	V OU
Supe Supe Symbol V _{IN} V _{ON/OFF} I L P _D TJ, T _{STG} ESD THERMA R _{0JA}	erSOT [™] 6 Parameter Input Voltage Range ON/OFF Voltage Range ON/OFF Voltage Range Load Current @ V _{DROP} =0.5V - Cor Maximum Power Dissipation Operating and Storage Temperatur Electrostatic Discharge Rating MIL Model (100pf/15000hm) L CHARACTERISTICS Thermal Resistance, Junction-to-A	e 25°C unless otherwise noted rtinuous (Note 1) - Pulsed (Note 1 & 3) (Note 2a) re Range -STD-883D Human Body rmbient (Note 2a)	a2 2 2 2 2 2 1 1	Vout,C1 R2 FDC6324L 3 - 20 1.5 - 8 1.5 2.5 0.7 -55 to 150 6 180	V ou Image: second secon

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FDC6324L Rev. D

Electrical Characteristics (T _A = 25°C unless otherwise noted)						
Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS					
I _{FL}	Forward Leakage Current	$V_{IN} = 20 \text{ V}, V_{ON/OFF} = 0 \text{ V}$			1	μA
I _{RL}	Reverse Leakage Current	$V_{IN} = -20$ V, $V_{ON/OFF} = 0$ V			-1	μA
ON CHARA	CTERISTICS (Note 3)					
V _{IN}	Input Voltage		3		20	V
V _{ON/OFF}	On/Off Voltage		1.5		8	V
V _{DROP}	Conduction Voltage Drop @ 1A	V_{IN} = 10 V, $V_{ON/OFF}$ = 3.3V		0.135	0.2	V
		V_{IN} = 5 V, $V_{ON/OFF}$ = 3.3 V		0.215	0.3	
I _L	Load Current	V_{DROP} = 0.2 V, V_{IN} = 10 V, V_{ONOFF} = 3.3 V	1			А
		V_{DROP} = 0.3 V, V_{IN} = 5 V, $V_{\text{ON/OFF}}$ = 3.3 V	1			

Notes:

1. V_{IN} =20V, V_{ONOFF} =8V, V_{DROP} =0.5V, T_A =25°C

2. R_{BA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BA} is guaranteed by design while $\mathrm{R}_{_{\mathrm{BCA}}}$ is determined by the user's board design.

$$\begin{split} P_D(t) &= \frac{T_T T_s}{R_{0,J}(t)} = \frac{T_T - T_s}{R_{0,J} \oplus R_{0,C}(t)} = I_D^2(t) \times R_{DQON)(\mathcal{M}_J} \\ \text{Typical $R_{0,h}$ for single device operation using the board layouts shown below on FR-4 PCB in astill air environment} \end{split}$$

a. 180°C/W when mounted on a 2oz minimum copper pad.



Scale 1 : 1 on letter size paper

3. Pulse Test: Pulse Width < 300µs, Duty Cycle< 2.0%

FDC6324L Rev. D





FDC6324L Rev. D



FDC6324L Rev. D

FDC6324L Load Switch Application



General Description

This device is particularly suited for computer peripheral switching applications where 20V input and 1A output current capability are needed. This load switch integrates a small N-Channel Power MOSFET (Q1) which drives a large P-Channel Power MOSFET (Q2) in one tiny SuperSOTTM-6 package.

A load switch is usually configured for high side switching so that the load can be isolated from the active power source. A P-Channel Power MOSFET, because it does not require its drive voltage above the input voltage, is usually more cost effective than using an N-Channel device in this particular application. A large P-Channel Power MOSFET minimizes voltage drop. By using a small N-Channel device the driving stage is simplified.

Component Values

R1	Typical 10k - 1M Ω	
R2	Typical 0-10kΩ	(optional)
C1	Typical 1000pF	(optional)

Design Notes

- R1 is needed to turn off Q2.
- R2 can be used to soft start the switch in the case the output capacitance Co is small.
- $R2 \leq$ should be at least 10 times smaller than R1 to guarantee Q1 turns on.
- By using R1 and R2 a certain amount of current is lost from the input. This bias current loss is given by the equation

 $I_{BIAS _LOSS} = \frac{Vin}{R1 \pm R2}$ when the switch is ON. $I_{BIAS _LOSS}$ can be minimized by large R1.

• R2 and C_{RSS} of Q2 make ramp for slow turn on. If excessive overshoot current occurs due to fast turn on, additional capacitance C1 can be added externally to slow down the turn on.

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Definition of Terms

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